2SC4927

Silicon NPN Triple Diffused

HITACHI

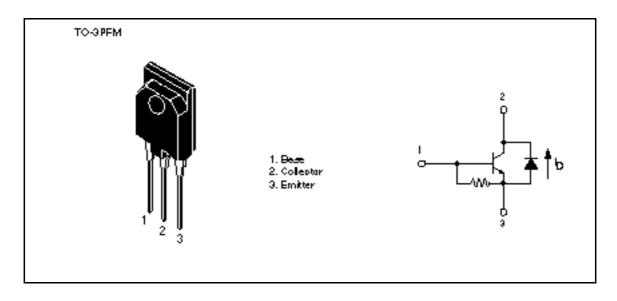
Application

TV/character display horizontal deflection output

Features

- High breakdown voltage
 - $V_{\text{CES}} = 1500 \ V$
- Built-in damper diode type
- Isolated package TO-3PFM

Outline





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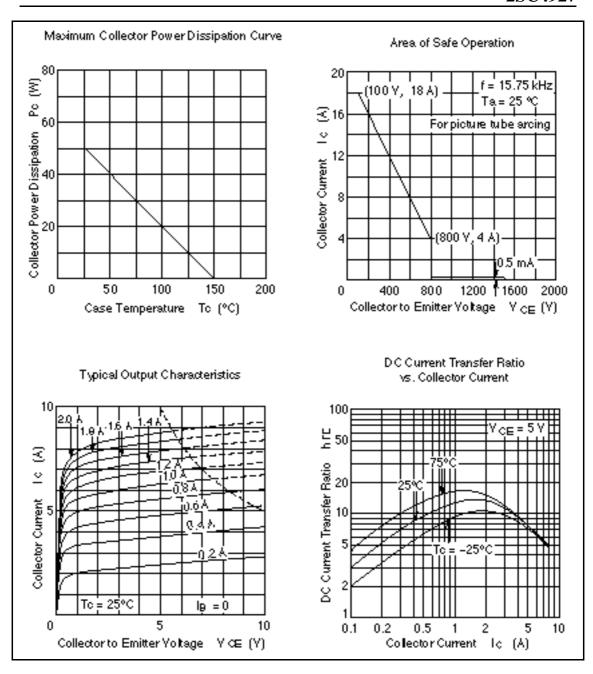
Absolute Maximum Ratings ($Ta = 25^{\circ}C$)

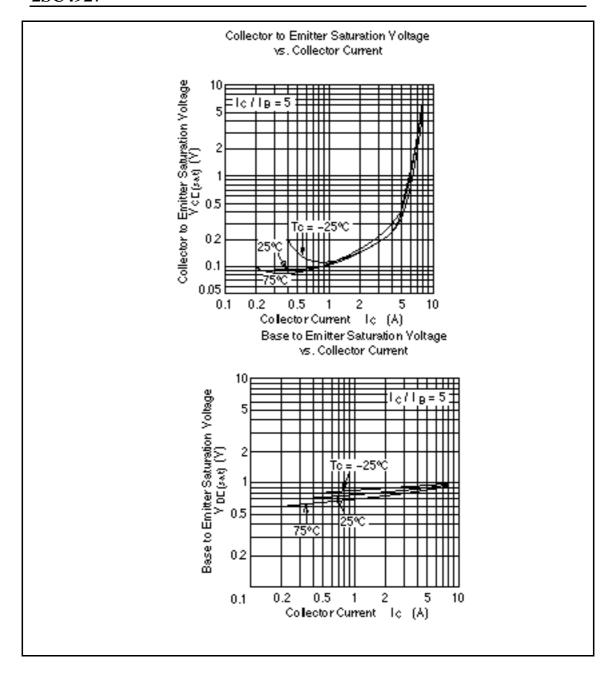
Item	Symbol	Ratings	Unit
Collector to emitter voltage	V _{CES}	1500	V
Emitter to base voltage	V_{EBO}	6	V
Collector current	I _c	8	A
Collector peak current	I _{C(peak)}	9	A
Collector surge current	I _{C(surge)}	18	A
Collector power dissipation	P _c *1	50	W
Junction temperature	Tj	150	°C
Storage temperature	Tstg	-55 to +150	°C
C to E diode forward current	I _D	8	A

Note: 1. Value at $T_c = 25$ °C.

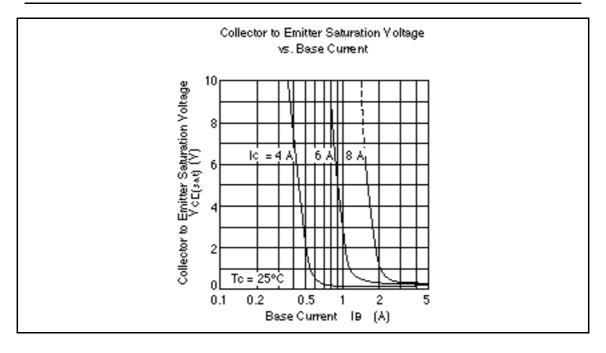
Electrical Characteristics ($Ta = 25^{\circ}C$)

Item	Symbol	Min	Тур	Max	Unit	Test conditions
Emitter to base breakdown voltage	$V_{(BR)EBO}$	6	_	_	V	$I_{\rm E} = 500 \text{ mA}, I_{\rm C} = 0$
Collector cutoff current	I _{CES}	_	_	500	μA	$V_{CE} = 1500 \text{ V}, R_{BE} = 0$
DC current transfer ratio	h _{FE}	_	_	25	_	$V_{CE} = 5 \text{ V}, I_{C} = 1 \text{ A}$
Collector to emitter saturation voltage	$V_{\text{CE(sat)}}$	_	_	5	V	$I_{\rm C} = 6 \text{ A}, I_{\rm B} = 1.2 \text{ A}$
Base to emitter saturation voltage	$V_{BE(sat)}$	_	_	1.5	V	$I_{\rm C} = 6 \text{ A}, I_{\rm B} = 1.2 \text{ A}$
C to E diode forward voltage	V_{ECF}	_	_	2.0	V	I _F = 8 A
Fall time	t _f	_	_	0.5	μs	$I_{CP} = 6 \text{ A}, I_{B1} = 1.2 \text{ A},$ $I_{B2} = -2.4 \text{ A}, f_{H} = 31.5 \text{ kHz}$





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